BUK7K5R1-30E

Dual N-channel 30 V, 5.1 m Ω standard level MOSFET

6 November 2013

Product data sheet

1. General description

Dual standard level N-channel MOSFET in an LFPAK56D (Dual Power-SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. Features and benefits

- Dual MOSFET
- Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with V_{GS(th)} of greater than 1 V at 175 °C

3. Applications

- 12 V Automotive systems
- Motors, lamps and solenoid control
- · Transmission control
- Ultra high performance power switching

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	30	V	
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	40	Α	
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	68	W	
Static characte	Static characteristics FET1 and FET2							
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 25 \text{ °C};$ Fig. 12		-	4.34	5.1	mΩ	
Dynamic chara	Dynamic characteristics FET1 and FET2							
Q_{GD}	gate-drain charge	$I_D = 10 \text{ A}; V_{DS} = 24 \text{ V}; V_{GS} = 10 \text{ V};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 14}}; \underline{\text{Fig. 15}}$		-	9	-	nC	



5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol	
1	S1	source1	8 7 6 5	D1 D1 D2 D2	
2	G1	gate1	1/		
3	S2	source2			
4	G2	gate2			
5	D2	drain2		S1 G1	
6	D2	drain2	l î î î	mbk725	
7	D1	drain1	1 2 3 4 LFPAK56D (SOT1205)		
8	D1	drain1	2		

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BUK7K5R1-30E	LFPAK56D	Plastic single ended surface mounted package (LFPAK56D); 8 leads	SOT1205			

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK7K5R1-30E	75E130

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	30	V
V_{DGR}	drain-gate voltage	R_{GS} = 20 kΩ; $T_j \ge 25$ °C; $T_j \le 175$ °C	-	30	V
V_{GS}	gate-source voltage	T _j ≤ 175 °C; DC	-20	20	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 1</u>	-	40	Α
		T _{mb} = 100 °C; V _{GS} = 10 V; <u>Fig. 1</u>	-	40	Α
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \mu s$; Fig. 4	-	340	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>	-	68	W

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Symbol	Parameter	Conditions		Min	Max	Unit
T _{stg}	storage temperature			-55	175	°C
T _j	junction temperature			-55	175	°C
T _{sld(M)}	peak soldering temperature			-	260	°C
Source-drai	n diode FET1 and FET2		'		,	,
Is	source current	T _{mb} = 25 °C		-	40	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	340	Α
Avalanche F	Ruggedness FET1 and FET2				'	
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 40 A; $V_{sup} \le 30 \text{ V}$; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; Fig. 3	[1][2]	-	228	mJ

- [1] Refer to application note AN10273 for further information
- [2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C

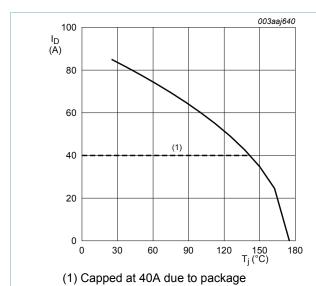


Fig. 1. Continuous drain current as a function of mounting base temperature

 $V_{GS} \ge 10V$

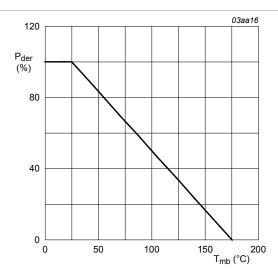
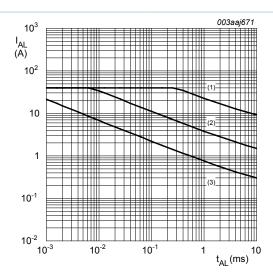


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}\text{C})}} \times 100 \,\%$$

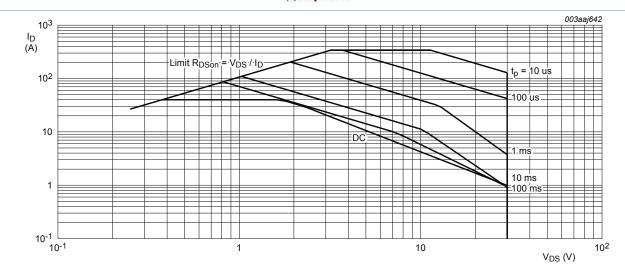
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Single-pulse and repetitive avalanche rating; avalanche current as a function of avalanche time, FET1 and FET2

- (1) Single-pulse; $T_j = 25 \,^{\circ}C$.
- (2) Single-pulse; $T_j = 150 \,^{\circ}C$.
 - (3) Repetitive.



Safe operating area; continuous and peak drain current as a function of drain-source voltage

 $T_{mb} = 25 \,^{\circ}C$; I_{DM} is single pulse

Thermal characteristics

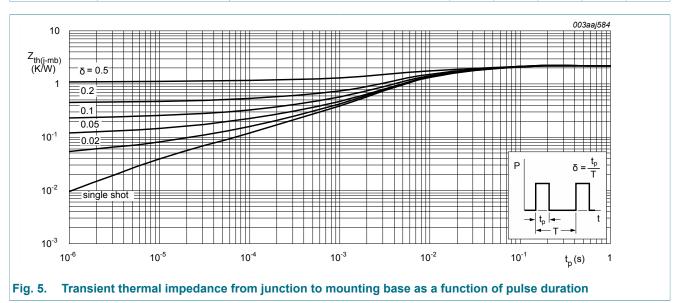
Table 6. **Thermal characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	-	2.21	K/W

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board	-	95	-	K/W



10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics FET1 and FET2		,			<u>'</u>
V _{(BR)DSS}	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	27	-	-	V
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	30	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 25 °C; Fig. 10; Fig. 11	2.4	3	4	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; Fig. 10; Fig. 11	1	-	-	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = -55 °C; Fig. 10; Fig. 11	-	-	4.5	V
I _{DSS}	drain leakage current	V _{DS} = 30 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μA
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	0.02	1	μA
I _{GSS}	gate leakage current	V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 25 \text{ °C};$ Fig. 12	-	4.34	5.1	mΩ
		V_{GS} = 10 V; I_D = 10 A; T_j = 175 °C; Fig. 12; Fig. 13	-	7.6	9.4	mΩ

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic c	haracteristics FET1 and FE	T2				
Q _{G(tot)}	total gate charge	I _D = 10 A; V _{DS} = 24 V; V _{GS} = 10 V;	-	31.1	-	nC
Q _{GS}	gate-source charge	T _j = 25 °C; <u>Fig. 14</u> ; <u>Fig. 15</u>	-	7.6	-	nC
Q _{GD}	gate-drain charge		-	9	-	nC
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz;	-	1764	2352	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 16</u>	-	422	506	pF
C _{rss}	reverse transfer capacitance		-	242	332	pF
t _{d(on)}	turn-on delay time	V_{DS} = 24 V; R_L = 2.4 Ω ; V_{GS} = 10 V;	-	9.5	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega; T_j = 25 °C; I_D = 10 A$	-	12.5	-	ns
t _{d(off)}	turn-off delay time		-	19.5	-	ns
t _f	fall time		-	13	-	ns
Source-dra	nin diode FET1 and FET2	1	ı	1	1	
V _{SD}	source-drain voltage	I _S = 10 A; V _{GS} = 0 V; T _j = 25 °C; <u>Fig. 17</u>	-	0.78	1.2	V
t _{rr}	reverse recovery time	$I_S = 10 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$	-	27.4	-	ns
Q _r	recovered charge	V _{DS} = 15 V; T _j = 25 °C	-	20.7	-	nC

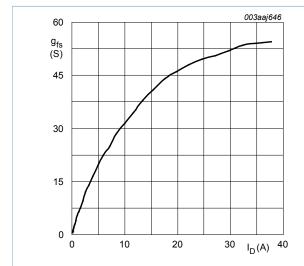


Fig. 6. Forward transconductance as a function of drain current; typical values

 $T_j = 25^{\circ}C; \ V_{DS} = 10V$

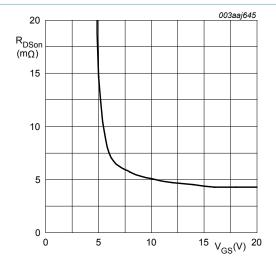
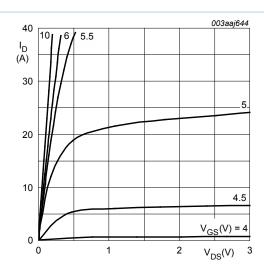


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

 $T_j = 25^{\circ}C; I_D = 10A$



 $T_i = 25 \,^{\circ}C; t_p = 300 \,\mu s$

Fig. 8. Output characteristics; drain current as a function of drain-source voltage; typical values

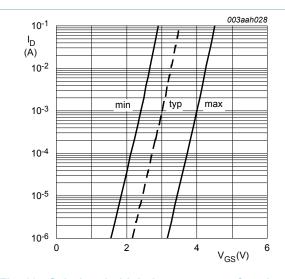


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25$$
°C; $V_{DS} = 5V$

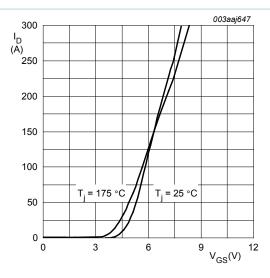


Fig. 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values

$$V_{DS} = 10V$$

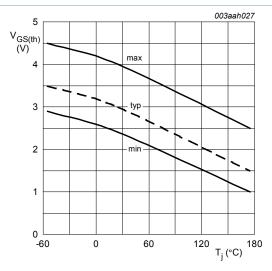


Fig. 11. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1 \text{ mA}; \ V_{DS} = V_{GS}$$

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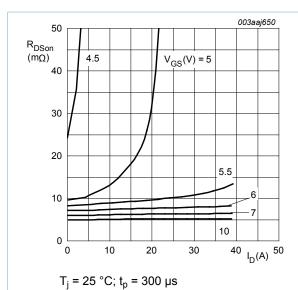


Fig. 12. Drain-source on-state resistance as a function of drain current; typical values

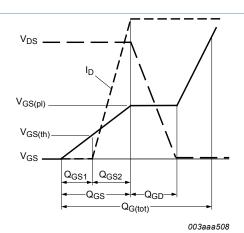


Fig. 14. Gate charge waveform definitions

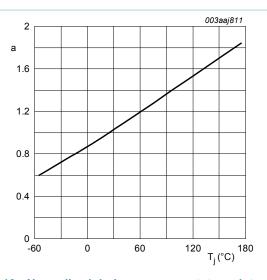


Fig. 13. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon (25^{\circ}C)}}$$

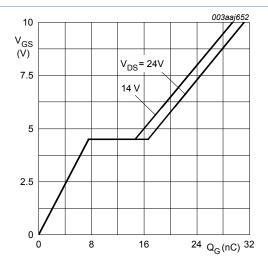


Fig. 15. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25^{\circ}C; I_D = 10A$$

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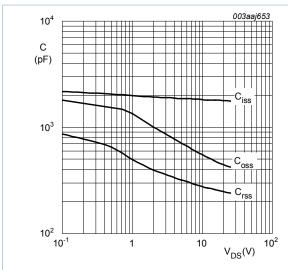
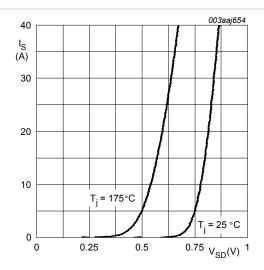


Fig. 16. Input, output and reverse transfer capacitances | Fig. 17. Source (diode forward) current as a function of as a function of drain-source voltage; typical values

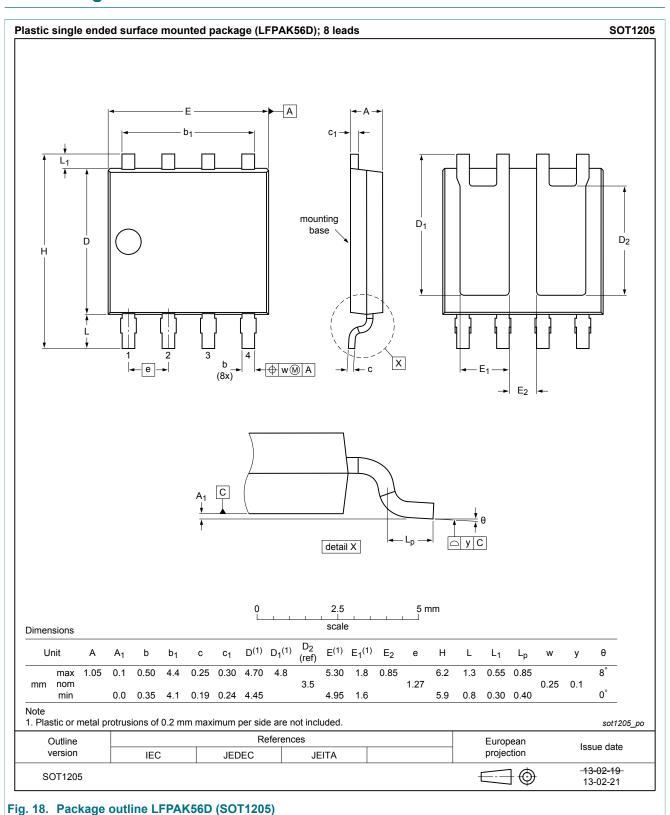
 $V_{GS} = \mathbf{0}V; f = \mathbf{1}MHz$



source-drain (diode forward) voltage; typical values

 $V_{GS} = 0V$

11. Package outline



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12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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